

FORM PTO-1449 U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE LIST OF REFERENCES CITED BY APPLICANT <i>(Use several sheets if necessary)</i>	ATTY. DOCKET NO. 12007-0074	SERIAL NO. 10/580,653
	APPLICANT Wolfgang STOLZ et al.	
	FILING DATE 03/30/2007	GROUP ART UNIT 2826

U.S. PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NO.	DATE	NAME	CLASS	SUB- CLASS	FILING DATE
---------------------	-----------------	------	------	-------	---------------	----------------

FOREIGN PATENT DOCUMENTS

	DOCUMENT NO.	DATE	COUNTRY	CLASS	SUB- CLASS	<u>TRANSLATION</u> YES NO PART.
--	-----------------	------	---------	-------	---------------	------------------------------------

OTHER REFERENCES (Including Author, Title, Date, Pertinent Pages, Etc.)

	1.	C. SETIAGUNG et al., "Very Low Threshold Current Density of 1.3 μ m-range GaInNAsSb/GaNAs 5QWs Lasers", The Furukawa Electric Co., Ltd., Yokohama R&D Laboratories, © 2002, IEEE, pgs. 39-40
	2.	E. GOUARDES et al., "GaInAs-GaInNAs-GaInAs Intermediate Layer Structure for Long Wavelength Lasers", <i>IEEE PHOTONICS TECHNOLOGY LETTERS</i> , vol. 14, No. 7, July 2002, pgs. 896-898
	3.	M. KAWAGUCHI et al., "Photoluminescence and Lasing Characteristics of 1.3 μ m GaInNAs/GaAsP/GaAs Strain-compensated Quantum Wells", <i>Compound Semiconductors</i> 2003, International Symposium, August 25-27, 2003, pgs. 72-73
EXAMINER /Kevin Quinto/		DATE CONSIDERED 07/15/2010
*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.		